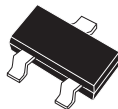


CBAS17

LOW VOLTAGE STABISTOR



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBAS17 type is a planar epitaxial silicon switching diode, designed for low voltage stabilizing applications.

Marking code is A91.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Peak Repetitive Forward Current	I_{FRM}	250	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_F	$I_F=0.1\text{mA}$	.580	.665	.680	V
V_F	$I_F=1.0\text{mA}$	.665	.745	.760	V
V_F	$I_F=5.0\text{mA}$	.725	.805	.820	V
V_F	$I_F=10\text{mA}$	.750	.825	.840	V
V_F	$I_F=100\text{mA}$	.870	.920	.960	V
I_R	$V_R=4.0\text{V}$			5.0	μA
C_T	$V_R=0, f=1\text{ MHz}$			140	pF

All dimensions in inches (mm).

